

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	89257	"thin film transistor" or TFT	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:48
L2	665698	transistor	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:48
L3	1176561	organic	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:48
L4	380191	(metallic or metal) with (source drain electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:49
L6	13707925	@ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:50
L8	461096	(adhere\$5 or fasten\$3 or glu\$3 or epox\$4 or past\$4 or tape\$2 or cement\$2 or bond\$3 or adhesive\$3) with (substrate or carrier)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:51
L9	2882	S104 and S105 and S106 and S107 and S111 and S109	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:51
L10	3073	S104 and S106 and S107 and S111 and S109	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:56
L11	48968	organic with (TFT or "thin film transistor" or semiconductor or channel)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:58
L12	1252	S104 and S106 and S107 and S111 and S109 and S114	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 11:58
L13	1	"5183780".pn.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/06/09 13:41
L23	328	(TFT or "thin film transistor") and ((coplanar or co-planar) with (transistor or TFT source drain gate electrode contact)) and @ad<"20030712" and organic	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 14:03

L24	0	(TFT or "thin film transistor") and ((coplanar or co-planar) with (transistor or TFT source drain gate electrode contact)) and @ad<"20030712" and organic and (electrodeposit or electro-deposit)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 14:35
L25	25	(TFT or "thin film transistor") and ((coplanar or co-planar) with (transistor or TFT source drain gate electrode contact)) and @ad<"20030712" and organic and (electrolytic or electroless)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 14:35
L26	303	S124 not S126	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/06/09 14:44
S1	1	"10563679"	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/03/05 11:24
S2	8	("20020008464" "20020172877" "20020093017" "6555411" "20020146893" "20030211665" "20020000614" "5388328"). pn.	US-PGPUB; USPAT	OR	OFF	2008/03/05 13:20
S3	93	257/E29.276.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:50
S4	829	257/E29.275.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:50
S5	7	257/E29.299.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:50
S6	70	257/E29.273.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:50
S7	446	257/E29.277.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:50
S8	319	257/E29.117.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:51
S9	910	257/E29.151.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:51
S10	170	257/289.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:51
S11	1173	257/40.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:51
S12	394	438/99.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:51
S13	1287	438/149.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:51

S14	1034	438/151.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:51
S15	187	257/359.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:51
S16	122	257/E31.041.ccls. and @ad<"20030712"	US-PGPUB; USPAT	OR	OFF	2008/03/05 14:52
S27	709	S4 not (S3 S5 S6 S8 S10 S12 S15 S16 S7)	US-PGPUB; USPAT	OR	OFF	2008/03/05 16:47
S32	733	S9 not (S3 S5 S6 S8 S10 S12 S15 S16 S7 S4)	US-PGPUB; USPAT	OR	OFF	2008/03/05 17:04
S33	978	S11 not (S3 S5 S6 S8 S10 S12 S15 S16 S7 S4 S9)	US-PGPUB; USPAT	OR	OFF	2008/03/05 17:23
S34	1009	S13 not (S3 S5 S6 S8 S10 S12 S15 S16 S7 S4 S9 S11)	US-PGPUB; USPAT	OR	OFF	2008/03/05 17:38
S35	530	S14 not (S3 S5 S6 S8 S10 S12 S15 S16 S7 S4 S9 S11 S13)	US-PGPUB; USPAT	OR	OFF	2008/03/05 18:05
S36	464	((metal or metallic) adj2 (source drain)) same (carrier) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 11:45
S37	189	438/161.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 12:16
S39	282	planar adj (TFT or "thin film transistor" or "thin-film transistor" or FET or "field effect transistor") and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 13:39
S40	15	planar adj (TFT or "thin film transistor" or "thin-film transistor" or FET or "field effect transistor") and @ad<"20030712" and ((metal or metallic) adj2 (source drain))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 13:42
S41	48	("3771026" "4014037" "4059461" "4063967" "4084986" "4086613" "4151008" "4154625" "4193183" "4198246" "4214918" "4229502" "4234358" "4240843" "4243433" "4267011" "4272880").PN. OR ("4339285").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/03/06 14:14
S42	22	("4234356" "4400715" "4542580" "4651410"). PN. OR ("5183780").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/03/06 14:27

S43	79	((metal or metallic) adj2 (source drain)) and ("conductive tape" or "conductive strip" or "conductive tapes" or "conductive strips" or "conductive carrier" or "conductive carriers") and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 14:31
S44	0	(planar adj (TFT or "thin film transistor" or "thin-film transistor" or FET or "field effect transistor")) and @ad<"20030712" and ((metal or metallic) adj2 (source or drain)) and ("conductive tape" or "conductive strip" or "conductive tapes" or "conductive strips" or "conductive carrier" or "conductive carriers")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 14:33
S45	0	(planar adj (TFT or "thin film transistor" or "thin-film transistor" or FET or "field effect transistor")) and ((metal or metallic) adj2 (source or drain)) and ("conductive tape" or "conductive strip" or "conductive tapes" or "conductive strips" or "conductive carrier" or "conductive carriers")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 14:33
S46	31	(planar) and ((metal or metallic) adj2 (source or drain)) and ("conductive tape" or "conductive strip" or "conductive tapes" or "conductive strips" or "conductive carrier" or "conductive carriers")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 14:34
S47	20	(planar) and ((metal or metallic) adj2 (source or drain)) and ("conductive tape" or "conductive strip" or "conductive tapes" or "conductive strips" or "conductive carrier" or "conductive carriers") and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 14:34

S48	1895	planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((place or deposit or remove) same (carrier or intermediate or vehicle or different transient) same substrate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:09
S49	343	planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((place or deposit or remove) with (carrier or intermediate or vehicle or different transient) with substrate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:10
S50	160	planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((place or deposit or remove) with (carrier or intermediate or vehicle or different transient) with substrate) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:10
S51	1043	planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((place or deposit or remove) same (carrier or intermediate or vehicle or different transient) same substrate) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:10
S52	3974	planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and (reverse) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:13

S53	2664	planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((remov\$5 or releas\$5 or separa\$5) same (carrier or intermediate or vehicle or different transient) same substrate) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:22
S54	9527	planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((remov\$5 or releas\$5 or separa\$5) same substrate) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:22
S55	573	planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((remov\$5 or releas\$5 or separa\$5) with (carrier or intermediate or vehicle or different transient) with substrate) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:23
S56	6798	planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((remov\$5 or releas\$5 or separa\$5) with substrate) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:23
S57	294	(method or process).ti. and planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((remov\$5 or releas\$5 or separa\$5) with (carrier or intermediate or vehicle or different transient) with substrate) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:24

S58	145	(method or process).ti. and planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((insulat\$4 near2 substrate) same (conduct\$3 near2 (carrier or substrate or tape))) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:34
S59	30	(method or process).ti. and planar and (FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((insulat\$4 adj substrate) same (conduct\$3 adj (carrier or substrate or tape))) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:37
S60	217	(FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((insulat\$4 adj substrate) same (conduct\$3 adj (carrier or substrate or tape))) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 15:59
S61	4	(FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((insulat\$4 adj substrate) same (conduct\$3 adj (carrier or tape))) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 16:00
S62	832	(FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((insulat\$4 adj substrate) same (conduct\$3 adj (layer or carrier))) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 16:33

S63	25	(FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((insulat\$4 adj substrate) same (transfer\$2 or fix\$2 or move\$2) same (conduct\$3 adj (layer or carrier))) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 16:34
S64	542	(FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") and ((substrate) same (transfer \$2 or fix\$2 or move\$2) same (conduct\$3 adj (layer or carrier))) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 16:36
S65	121	(FET or "field effect transistor" or "field-effect transistor" or TFT or "thin film transistor" or "thin-film transistor") same ((substrate) same (transfer \$2 or fix\$2 or move\$2) same (conduct\$3 adj (layer or carrier))) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/06 16:36
S66	1114	(adhe\$5 or fix or epoxy) with (substrate) with (transistor)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 10:13
S67	1114	(adhe\$5 or fix or expoy) with (substrate) with (transistor)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 10:13
S68	1297	(adhe\$5 or fix or epoxy) with (substrate) with (transistor)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 10:14
S69	1016	(adhe\$5) with (substrate) with (transistor)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 10:14
S70	558	(adhere or adhesive) with (substrate) with (transistor)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 10:14
S71	325	(adhere or adhesive) with (substrate) with (transistor) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 10:15
S72	124	((adhere or adhesive) with (substrate) with (transistor) and @ad<"20030712") and organic	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 10:37

S73	42	((adhere or adhesive) with (substrate) with (transistor) and @ad<"20030712") and organic and planar	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 10:46
S74	5	((metal or metallic) adj (source or drain)) OR ((source or drain) adj (electrode))) and (((adhere or adhesive) with (substrate) with (transistor or FET or MOS or MOSFET or TFT)) same planar)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 11:17
S75	1	"5183780".pn.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 11:22
S76	199	("active matrix display" or "active matrix displays") and (electrolytic or electro-deposit or electro-deposition)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 11:45
S77	88	("active matrix display" or "active matrix displays") and ((electrolytic or electro-deposit or electro-deposition) with (metal or electrode))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 11:45
S78	62	("active matrix display" or "active matrix displays") and ((electrolytic or electro-deposit or electro-deposition) with (metal or electrode)) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 11:46
S79	1	("active matrix display" or "active matrix displays") and ((electro-deposit or electro-deposition) with (metal or electrode)) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 11:47
S80	1717	"organic thin film transistor"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 13:23
S81	425	S80 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 13:24
S83	74	S81 and planar	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 13:24
S84	2152	"organic thin film transistor" or "organic TFT"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 13:50

S86	521	S84 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/03/07 14:15
S87	34	("4106951" "5468519" "5500537").PN. OR ("6326640").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/03/07 15:05
S88	2	OJFET	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2008/03/07 15:41
S89	331	438/82.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/03/07 15:48
S90	6	(438/82.ccls. or 438/99. ccls.) and ((adhere or adhesive) with (substrate) with (transistor))	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/03/07 16:25
S91	0	438/ For135.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/03/07 16:33
S92	0	437/1.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/03/07 16:34
S93	108	257/E51.007.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/03/07 16:37
S94	24	(organic near4 transistor) and ((conductive adj2 (substrate or layer or film)) with (transfer\$4)) and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/03/07 16:42
S95	37340	(Hewlett Packard).as.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2008/03/07 16:53
S96	978	S95 and transistor and substrate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 16:53
S97	596	S96 and conductive	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 16:54
S98	407	S95 and transistor and (substrate same conductive)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 16:55
S99	34	S95 and transistor and (substrate same conductive same transfer\$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 17:01
S100	218	Rudin.in.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2008/03/07 17:12
S103	3	("20020045289" "6344660" "20030059984").pn.	US-PGPUB; USPAT	OR	ON	2008/03/07 17:28

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